

LED22-PR



TECHNICAL DATA

Mid-Infrared Light Emitting Diode

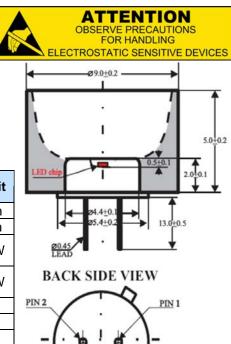
Light Emitting Diodes with central wavelength 2.25 µm series are based on heterostructures grown on GaSb substrates. They are developed for using in optical gas sensors and medical diagnostics. LED22-PR has a stable ouput power and a lifetime more then 80000 hours.

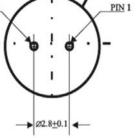
Features

- Structure: GaInAsSb/AlGaAsSb
- Peak Wavelength: typ. 2.25 µm
- Optical Ouput Power: typ. 1.1 mW qCW
- Package: TO-18, with PR and without window

Specifications

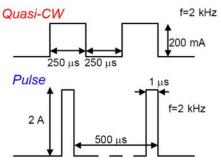
ltem	Condition	Rating			Unit
		Min.	Тур.	Max.	Unit
Peak Wavelength	T=300 K	2.20	2.25	2.29	μm
FWHM	150 mA CW	150	200	250	nm
Quasi-CW Optical Power	200 mA qCW	0.9	1.1	1.3	mW
Pulsed Optical Power	1 A	25	28	30	mW
Switching Time	T=300 K	10	30	50	ns
Operation Voltage	200 mA qCW				V
Operating Temperature	-240 +50				°C
Emitting Area	300x300				μm
Soldering Temperature	180				°C
Package	TO-18, with parabolic reflector and without window				





(Unit: mm)

Operating Regime



Quasi-CW

- Maximum current 220 mA
- Recommended current 150-200mA

Pulsed

 Maximum current 1 A (puls lenght 500 ns, repetition rate 2kHz)



Typical Performance Curves

